

Freescale Semiconductor Mask Set Errata

MSE908AP64_0L47P Rev. 0, 1/2007

Mask Set Errata for Mask 0L47P

Introduction

This mask set errata applies to the mask 0L47P for these products:

- MC68HC908AP64
- MC68HC908AP32
- MC68HC908AP16
- MC68HC908AP8

MCU Device Mask Set Identification

The mask set is identified by a 5-character code consisting of a version number, a letter, two numerical digits, and a letter, for example 0L47P. All standard devices are marked with a mask set number and a date code.





SPI Slave Mode Operation Issue

SE122-SPI-slave

Description

This errata describes a voltage and noise sensitivity issue with the SPI while in slave mode. The SPI, while in slave mode, can experience transmission errors resulting in simultaneous receive and transmit errors. This is attributed to noise corrupting the slave clock input to the SPI module.

Workaround

You must use fault-tolerant software and/or hardware handshaking protocol that can detect errant data and request re-transmission of the data from the SPI master. The SPI master in-turn must be able to detect anomalous data from the slave SPI and request re-transmission of the data from the SPI slave.

NOTE:

Use of the SPI in slave mode at a nominal voltage of 3.3 V virtually eliminates the issue. All designs should incorporate decoupling capacitors very close to the MCU to avoid noise injection from the application.

Brief Pause on Standard Input/Output Pins during Power-On-Reset

SE95-I/O_POR

Description

During a power-on-reset, a brief pulse may appear on the following I/O pins: PTA0-PTA7, PTB4-PTB7, PTC0-PTC5, and PTD0-PTD7. The brief pulse, which is due to the turn-on delay of the internal regulator, can drive active-high output circuits (for example, relays or NPN transistors) momentarily. The turn-on delay is greater for slow rising VDD supplies. Input circuits are not affected.

Workaround

Add an external RC filter to the output port pin, where necessary, for control sensitive applications.

In applications where these brief pulses could cause undesirable effects, add an external RC filter between the MCU output pin and the circuit that it drives.

ROM-Resident Routines

SE72-ROM

Do not use the following ROM-resident routines:

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- ERARNGE
- MON_ERARNGE
- EE_WRITE
- EE_READ

A coding error has been found in the these routines which may cause accidental erasure of the reset vector at \$FFFF.

Workaround for EE_WRITE and EE_READ

The workaround is to have routines stored in the user FLASH area. An implementation is provided in the Motorola application note: *Using FLASH as EEPROM on the MC68HC908GP32*, which can be downloaded from

http://e-www.motorola.com/files/microcontrollers/doc/app_note/AN2183.pdf.

Workaround for ERARNGE and MON_ERARNGE

The following routine can be used as a workround for ERARNGE and MON_ERARNGE. The routine is intended to be stored in an area of FLASH, loaded and executed in RAM when called.

```
*# Includes
include
                  "ap64R2.asm"
                                   ; register and bit equates for AP64
*# Variables
.first SECTION short
; V ADDRH IN
           ds.b
                  2
V ADDRH IN
           ds.b
V ADDRL IN
           ds.b
V_FLASH_ADDR
                  2
           ds.b
V TEST COUNT
           ds.b
                  2
RAMPTR
           equ
                  *
V RAMPTR H
           ds.b
                  1
V RAMPTR L
           ds.b
                  1
Q RAM Blk Erase equ
; CONFIG1
           equ
                  $001F
; PORTA
                  $0
           equ
; DDRA
           equ
                  $04
```

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ROM-Resident Routines SE72-ROM

FLCR	equ	\$FE08			
b ERASE	equ	•			
_	b_HVEN equ		3		
FLBPR	_		\$FE09		
I DDIII	equ	Ŷ1 2 03			
MORVALUE	equ	%1111111			
PRGRNGE	equ	\$FC34			
LDRNGE	equ				
ERARNGE	equ				
WRITE EE	equ				
-		u \$FD5B			
_	- 4	,			
;RAMPTR	equ	\$100			
BUSSPEED	equ		; using 10MHz oscillator CLK input		
DATASIZE	equ		, and grant the state of the st		
ERASEBLOC					
; ENDBLOCK					
, ENDELOGIC	cqu	γ1 000			
; ENDBLOCK	equ	\$E000			
ENDBLOCK	equ				
BLOCKSIZE					
DECCRITE	cqu	Ş200			
TESTCOUNT	equ	\$20			
TESTCOONT	cqu	720			
FLASHSTAR'	T equ	\$860			
RAM BEGIN	_				
_					
RAM_END	equ	\$85F			
d - + - C	DODITON.				
*####### *# Functi	ons	#######################################			
*####### *# Functi *########	######### ons ###########	##############			
*####### *# Functi *#######	######### ons ######### def mai	########### n			
*####### *# Functi *####### x	######### ons ######### def mai def DUM	########### n MY_ISR			
*####### *# Functi *####### x	######### ons ######### def mai def DUM	########### n			
*####### *# Functi *####### x x	########## ons ########## def mai def DUM def IRQ	########### n MY_ISR			
*####### *# Functi *####### x x	########## ons ########## def mai def DUM def IRQ	############# n MY_ISR _ISR			
*####### *# Functi *###### x x	########## ons ########## def mai def DUM def IRQ	############# n MY_ISR _ISR			
*####### *# Functi *###### x x x o main:	########## ons ########## def mai def DUM def IRQ	############# n MY_ISR _ISR			
*####### *# Functi *####### x x x o main:	########## ons ########## def mai def DUM def IRQ rg FLA	############# n MY_ISR _ISR SHSTART			
*####### *# Functi *####### x x x o main:	######################################	############# n MY_ISR _ISR SHSTART	##		
*####### *# Functi *###### x x x o main:	######################################	############# n MY_ISR _ISR SHSTART	##		
*####### *# Functi *###### x x x o main:	######################################	############## n MY_ISR _ISR SHSTART	##		
*####### *# Functi *###### x x x o main:	######################################	############### n MY_ISR _ISR SHSTART FF	##		
*###### *# Functi *###### x x x x o o main:	######################################	############### n MY_ISR _ISR SHSTART FF	##		
*####### *# Functi *###### x x x o main: s m	######################################	############### n MY_ISR _ISR SHSTART FF b,CONFIG1 1,CONFIG2	## ; reset COP		
*####### *# Functi *###### x x x o main: s m m t	######################################	######################################	## ; reset COP		
*####### *# Functi *####### x x x o main: s m m t:	######################################	######################################	<pre>## ; reset COP ; reset stack ptr to end of RAM</pre>		
*####### *# Functi *####### x x x o main: s m m t:	######################################	######################################	## ; reset COP		
*####### *# Functi *###### x x x o main: s m m t:	######################################	######################################	<pre>## ; reset COP ; reset stack ptr to end of RAM</pre>		
*####### *# Functi *###### x x x x O main: s m m t: 1.	######################################	######################################	<pre>## ; reset COP ; reset stack ptr to end of RAM</pre>		
*####### *# Functi *###### x x x x O main: s m m t: 1.	######################################	######################################	; reset COP ; reset stack ptr to end of RAM ; protect vector table only		
*####### *# Functi *###### x x x x o main: s m m 1. t: 1. s	######################################	######################################	; reset COP ; reset stack ptr to end of RAM ; protect vector table only		

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```
*----*
      ldhx
             #(RAM END-RAM BEGIN)
Clear RAM:
      clr
             (RAM BEGIN-1),X
      dbnzx
             Clear_RAM
*--- erase block ------
erase1:
      ldhx
             #ERASEBLOCK
                                        ; load block addres to V FLASH ADDR
      sthx
             V_FLASH_ADDR
      pshh
                                         ; "h" content will be corrupted in the jump
RAM routine
      jsr
             FLASH ERASE
      pulh
*--- erase have been done -----
finish all:
      bset
             0, PORTA
      nop
      nop
      bclr
             0, PORTA
             finish_all
      bra
; Block Erase
FLASH ERASE:
      bsr
            BlkErase2RAM
                                        ; copy block erase routine to RAM
            V FLASH ADDR
      ldhx
                                        ; load H:X with the block address
             #(1<<b ERASE)
                                        ; MUST load Acc with b_ERASE
      lda
      jsr
             Q RAM Blk Erase
                                        ; execute block erase in RAM
      rts
BlkErase2RAM:
      clrh
      ldx
            #Blk Erase Len
                                        ; get blk erase routine length
                                        ; get blk erase routine length
      ldhx
           #Blk Erase Len
                                        ; NB: Assume "Blk_Erase_Len" is one byte long
BE2RAM1:
      1 da
            (Block Erase-1),x
                                        ; load from FLASH
            (Q_RAM_Blk_Erase-1),x
      sta
                                        ; copy to RAM
      dbnzx
             BE2RAM1
                                         ; NB: Assume "Blk Erase Len" is one byte long
                                         ; need modification if length over 1 byte
      rts
Block Erase:
      sta
             FLCR
                                         ; set ERASE bit
      sta
                                         ; write any data to block
             ,x
```

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ROM-Resident Routines SE72-ROM

```
Dly_5us
      bsr
      lda
            FLCR
      ora
            #(1<<b_HVEN)
      sta
            FLCR
                                       ; set HVEN bit
* ------ *
      ldx
            #20
                                       ; (2)
Blk Erase Time:
      bsr
            Dly_1ms
                                       ;[14]
      dbnzx
           Blk_Erase_Time
                                       ; (3)
      ldhx
            #FLCR
      lda
            #%00001000
                                       ; clear ERASE bit
      sta
            , x
      bsr
            Dly_5us
      clr
                                       ; clear HVEN bit
            , x
      rts
Blk Erase Exit:
* ----- *
; For 2.5MHz bus
Dly_5us:
                        ; [4] cycles
            #2
      lda
                         ; [2]
      dbnza
            $
                         ; [3]
      rts
                         ; [4]
Dly_1ms:
                         ; [4] cycles
      lda
            #255
                         ; [2]
            PORTB, PORTB
                         ; dummy for 5 bus clk
      mov
      dbnza
                         ; [3]
                         ; [4]
      rts
Dly 5us Exit:
Blk_Erase_Len equ (Dly_5us_Exit - Block_Erase)
*******
* dummy interrupt service routine
DUMMY ISR:
      rti
*******
* IRQ interrupt service routine
********
IRQ ISR:
            ACK1, INTSCR1 ; IRQ acknowledge
      bset
      rti
*--- block to be erased -----
      org
            ERASEBLOCK
      dc.w
            $0000,$0000,$0000,$0000,$0000,$0000,$0000
      dc.w
            $0000,$0000,$0000,$0000,$0000,$0000,$0000
```

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FLASH Memory Erasing and Programming SE71-FLASH

```
dc.w
              $0000,$0000,$0000,$0000,$0000,$0000,$0000
      dc.w
              $0000,$0000,$0000,$0000,$0000,$0000,$0000
*********
*MOR register
******
      ORG
             MOR
             MORVALUE
```

dc.b

FLASH Memory Erasing and Programming

SE71-FLASH

To maintain data integrity in the FLASH memory, do not access FLASH memory locations that are not intended for program or erase once the high voltage enable bit is set (HVEN = 1). If the COP is enabled, a COP counter reset (write to \$FFFF) should be performed before setting the HVEN bit.

FLASH Page Erase Operation

Do not access any other FLASH locations between steps 4 to 8. Do not reset the COP counter between steps 4 to 8.

Set the ERASE bit and clear the MASS bit in the FLASH control register.

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Phase Lock Loop Stability SE70-PLL

- 2. Write any data to any FLASH location within the page address range desired.
- 3. Wait for a time, t_{nvs} (5 μ s).
- 4. Set the HVEN bit.
- 5. Wait for a time t_{erase} (20 ms).
- 6. Clear the ERASE bit.
- 7. Wait for a time, t_{nvh} (5 μ s).
- 8. Clear the HVEN bit.
- 9. After time, t_{rcv} (1 μ s), the memory can be accessed in read mode again.

FLASH Program Operation

Do not access any FLASH locations that are not intended for programming between steps 4 to 11. Do not reset the COP counter between steps 4 to 11.

- 1. Set the PGM bit. This configures the memory for program operation and enables the latching of address and data for programming.
- 2. Write any data to any FLASH location within the address range of the row to be programmed.
- 3. Wait for a time, t_{nvs} (5 μ s).
- 4. Set the HVEN bit.
- 5. Wait for a time, t_{pas} (10 μ s).
- 6. Write data to the FLASH location to be programmed.
- 7. Wait for time, t_{proq} (20 μ s to 40 μ s).
- 8. Repeat steps 6 and 7 until all bytes within the row are programmed.
- 9. Clear the PGM bit.
- 10. Wait for time, t_{nvh} (5 μ s).
- 11. Clear the HVEN bit.
- 12. After time, t_{rcv} (1 μ s), the memory can be accessed in read mode again.

Phase Lock Loop Stability

SE70-PLL

Do not use the PLL under these settings: AUTO = 1; or AUTO = 0 and \overline{ACQ} = 1.

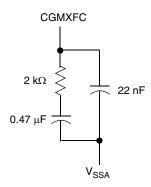
The clock generator module's PLL does not meet stability requirements when running in automatic bandwidth control mode or manual tracking mode. In these modes, the VCO output clock can become erratic, causing unpredictable MCU clocks, and resulting in possible MCU failure.

To overcome this problem, the PLL must be used in manual acquisition mode (AUTO = 0 and \overline{ACQ} = 0). As a result, there is no PLL lock detector, nor lock interrupt. The LOCK and PLLF bits are meaningless.

Follow this procedure for using the PLL:

1. Use the following external filter components:





- 2. Configure the PLL to the desired frequency.
- 3. Clear AUTO and ACQ bits.
- 4. Set PLLON bit to turn on the PLL.
- 5. Wait 50ms for the PLL to lock.
- 6. Set BCS bit to select the VCO clock as the reference clock for the MCU.

ADC Accuracy at Zero Volt Input

SE68-ADC

The 10-bit ADC conversion result for 0V input (zero input reading) is \$000, \$001, \$002, or \$003; not the specified \$00 or \$01. With inputs of 5 mV and above, the ADC is within the specified accuracy of $\pm 1.5 \text{ LSB}$ (see **Figure 1**).

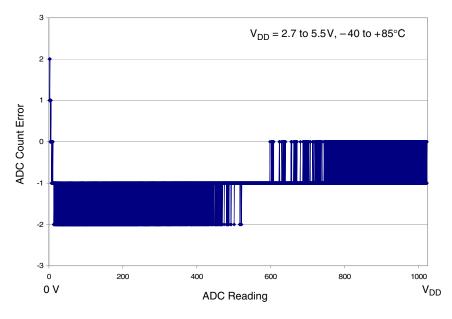


Figure 1. Typical ADC Error Count

External Bypass Capacitor Connection on V_{REG} Pin SE69-VREG

External Bypass Capacitor Connection on V_{REG} Pin

SE69-VREG

Do not use a larger value than the recommended 100 nF bypass capacitor connection between the V_{REG} and V_{SS} pins. Large capacitor values can cause the V_{REG} voltage to fall too slowly during a power-down. The V_{REG} voltage must be allowed to fall below 100 mV before the MCU is powered up again. This allows the power-on reset circuit to rearm properly on power-up.

Low-Voltage Inhibit Reset in Stop Mode

SE67-LVI

An internal reset occurs when entering stop mode if the LVI control bits are configured as shown in the table below:

CONFIG1 Register (\$001F)					
Bit 4	Bit 3	Bit 6	Bit 5		
LVIPWRD	LVIREGD	LVISTOP	LVIRSTD		
X	Х	0	0		
1	1	Х	0		

X = don't care

LVIPWRD=1 is V_{DD} LVI circuit disabled.

LVIREGD=1 is V_{REG} LVI circuit disabled.

LVISTOP=0 is LVI disabled in stop mode.

LVIRSTD=0 is LVI resets enabled.

To enter stop mode with LVI disabled, set LVIRSTD=1 before entering stop mode. This will not cause an internal reset and also reduces the stop I_{DD} to a minimum.